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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10042060	01/07/2002	117		1765	ANDERSON

**APPLICANTS: Kuhn Harald; Stein Rene; Voelkl Johannes;

**CONTINUING DATA VERIFIED:

THIS APPLICATION IS A CON OF PCT/DE00/02174 07/04/2000

** FOREIGN APPLICATIONS VERIFIED:

GERMANY 199 31 333.4 07/07/1999

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input checked="" type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO
35 USC 119 conditions met <input checked="" type="checkbox"/> yes <input type="checkbox"/> no		GR99P3456
Verified and Acknowledged Examiners's initials <i>MM</i>		
TITLE : Method for the sublimation growth of an SiC single crystal, involving heating under growth pressure		

U.S. DEPT. OF COMM./PAT & TM-PTO-436L (Rev. 12-94)

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NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED		
		Total Claims		Print Claim for O.G.
Assistant Examiner		DRAWING		
Amount Due		Sheets Drwg.	Figs. Drwg.	Print Fig.
Date Paid				
Primary Examiner		Application Examiner		
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE		
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